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# 2SD2101

Silicon NPN Triple Diffused

# HITACHI

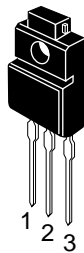
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## Application

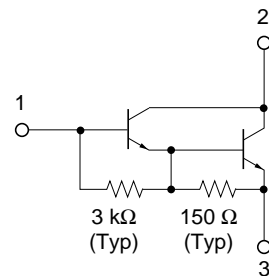
Low frequency power amplifier

## Outline

TO-220FM



- 1. Base
- 2. Collector
- 3. Emitter



## 2SD2101

### Absolute Maximum Ratings (Ta = 25°C)

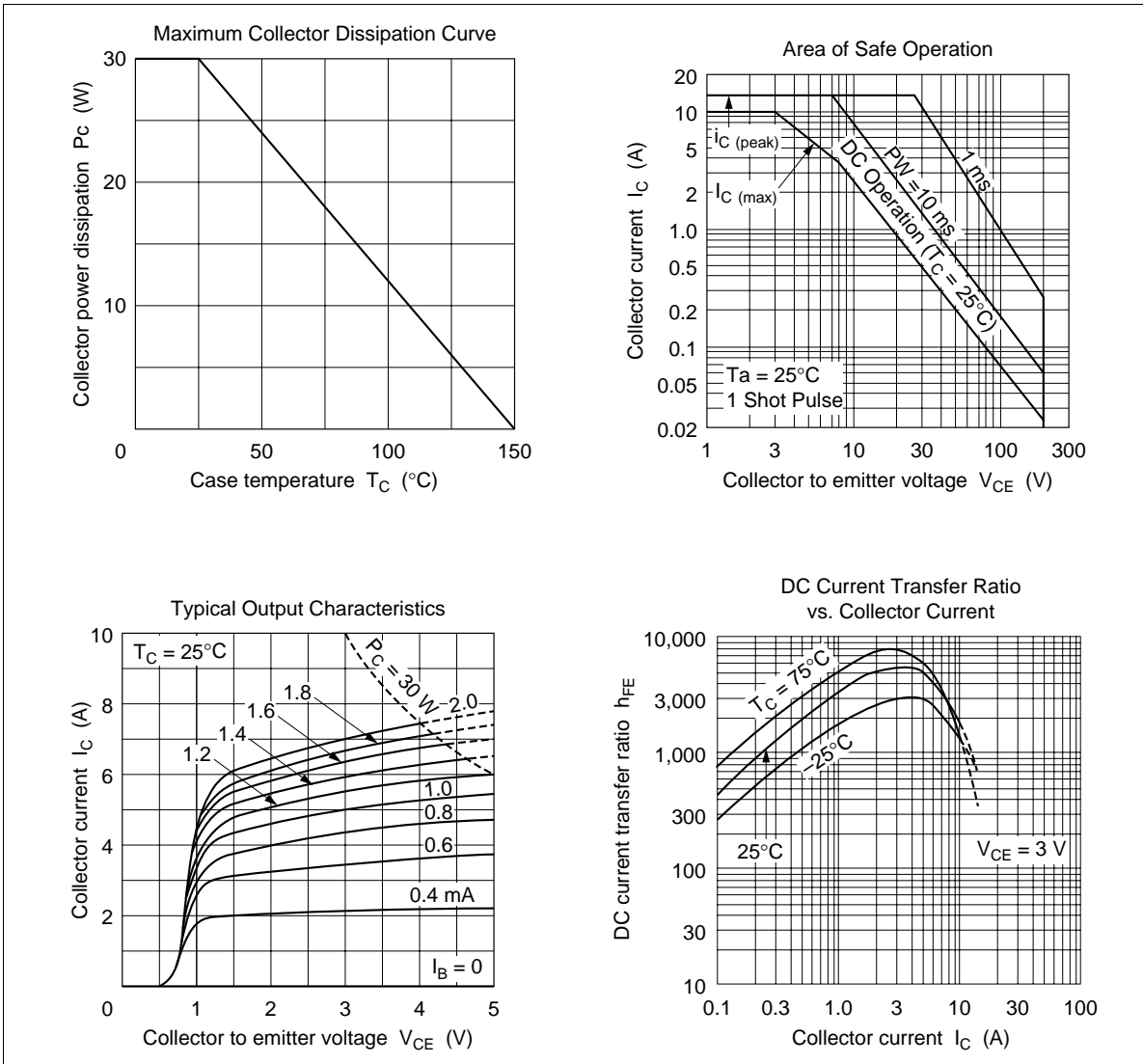
Item	Symbol	Rating	Unit
Collector to base voltage	$V_{CBO}$	200	V
Collector to emitter voltage	$V_{CEO}$	200	V
Emitter to base voltage	$V_{EBO}$	7	V
Collector current	$I_C$	10	A
Collector peak current	$I_{C(peak)}$	15	A
Collector power dissipation	$P_C$	2	W
	$P_C^{*1}$	30	
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

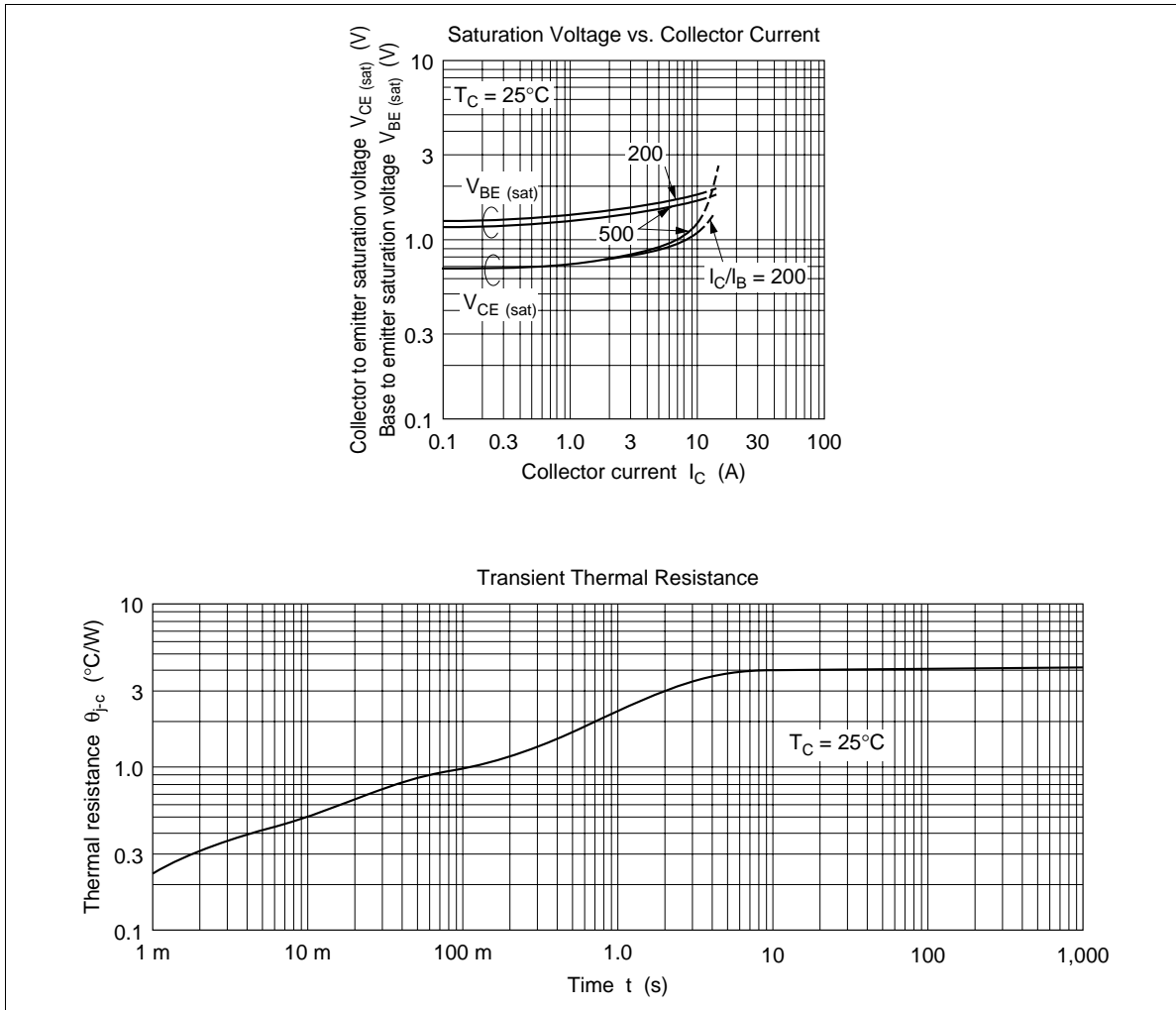
Note: 1. Value at  $T_C = 25^\circ\text{C}$ .

### Electrical Characteristics (Ta = 25°C)

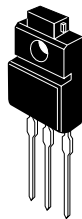
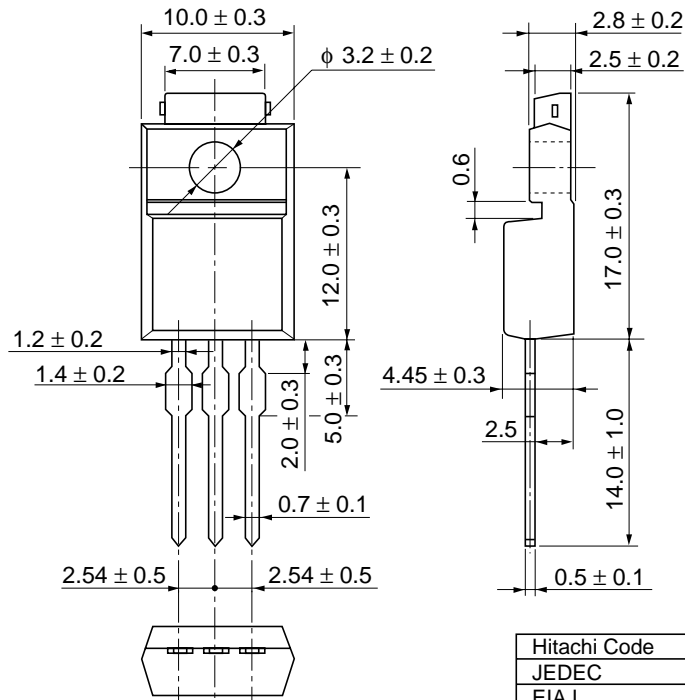
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	200	—	—	V	$I_C = 0.1 \text{ mA}, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	200	—	—	V	$I_C = 25 \text{ mA}, R_{BE} = \infty$
Collector to emitter sustain voltage	$V_{CEO(SUS)}$	170	—	—	V	$I_C = 5 \text{ A}, L = 5 \text{ mH}$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 50 \text{ mA}, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	10	$\mu\text{A}$	$V_{CB} = 180 \text{ V}, I_E = 0$
	$I_{CEO}$	—	—	50		$V_{CE} = 180 \text{ V}, R_{BE} = \infty$
DC current transfer ratio	$h_{FE}$	1500	—	—		$V_{CE} = 3 \text{ V}, I_C = 5 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	—	1.5	V	$I_C = 5 \text{ A}, I_B = 10 \text{ mA}^{*1}$
	$V_{CE(sat)2}$	—	—	3.0		$I_C = 10 \text{ A}, I_B = 100 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	2.0	V	$I_C = 5 \text{ A}, I_B = 10 \text{ mA}^{*1}$
	$V_{BE(sat)2}$	—	—	3.5		$I_C = 10 \text{ A}, I_B = 100 \text{ mA}^{*1}$

Note: 1. Pulse test.





Unit: mm



Hitachi Code	TO-220FM
JEDEC	—
EIAJ	Conforms
Weight (reference value)	1.8 g

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# HITACHI

## Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan  
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL      North America      : <http://semiconductor.hitachi.com/>  
             Europe                : <http://www.hitachi-eu.com/hel/ecg>  
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## For further information write to:

Hitachi Semiconductor  
(America) Inc.  
179 East Tasman Drive,  
San Jose, CA 95134  
Tel: <1> (408) 433-1990  
Fax: <1> (408) 433-0223

Hitachi Europe GmbH  
Electronic components Group  
Dornacher StraÙe 3  
D-85622 Feldkirchen, Munich  
Germany  
Tel: <49> (89) 9 9180-0  
Fax: <49> (89) 9 29 30 00  
  
Hitachi Europe Ltd.  
Electronic Components Group.  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA, United Kingdom  
Tel: <44> (1628) 585000  
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.  
16 Collyer Quay #20-00  
Hitachi Tower  
Singapore 049318  
Tel: 535-2100  
Fax: 535-1533

Hitachi Asia Ltd.  
Taipei Branch Office  
3F, Hung Kuo Building, No.167,  
Tun-Hwa North Road, Taipei (105)  
Tel: <886> (2) 2718-3666  
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.  
Group III (Electronic Components)  
7/F., North Tower, World Finance Centre,  
Harbour City, Canton Road, Tsim Sha Tsui,  
Kowloon, Hong Kong  
Tel: <852> (2) 735 9218  
Fax: <852> (2) 730 0281  
Telex: 40815 HITEC HX

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